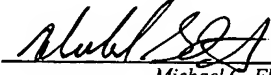


IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:	§	
Fernando Gonzalez et al.	§	
	§	Group Art Unit: Unassigned
Prior Application Serial No.: 09/906,122	§	
Prior Application Filed: July 16, 2001	§	
	§	
Serial No.: Unassigned	§	Examiner: Unassigned
	§	
Filed: Herewith	§	
	§	
For: METHOD FOR FABRICATING AN	§	Atty Docket: MCRO:017—7/FLE
ARRAY OF ULTRA-SMALL	§	94-0358.07
PORES FOR CHALCOGENIDE	§	
MEMORY CELLS	§	

**Mail Stop Patent Application**  
 Commissioner for Patents  
 P.O. Box 1450  
 Alexandria, VA 22313

<b>EXPRESS MAIL MAILING LABEL</b>	
NUMBER:	EV 365 157 589
DATE OF DEPOSIT:	February 18, 2004
<i>Pursuant to 37 C.F.R. § 1.10, I hereby certify that I am personally depositing this paper or fee with the U.S. Postal Service, "Express Mail Post Office to Addressee" service on the date indicated above in a sealed envelope (a) having the above -numbered Express Mail label and sufficient postage affixed, and (b) addressed to the Commissioner for Patents, Alexandria, VA 22313.</i>	
February 18, 2004	
Date	Michael G. Fletcher

Sir:

**INFORMATION DISCLOSURE STATEMENT**  
**PURSUANT TO 37 C.F.R. §§ 1.97(b)(1) AND 1.98, INCLUDING 1.98(d)**

In compliance with the duty of disclosure under 37 C.F.R. § 1.56(a), Applicants respectfully request that this Information Disclosure Statement be entered and that the references listed on the PTO-1449 Form, filed herewith, be considered by the Examiner and made of record. The presently filed application is a Divisional of application Serial No. 09/906,122, filed on July 16, 2001, which is a Divisional of application Serial No. 09/309,622, filed May 11, 1999, which is a Continuation of application Serial No. 08/846,728, filed April 30, 1997, which issued as U.S.P.N. 6,002,140 on December 14, 1999, which is a Divisional of application Serial No. 08/473,077, filed June 7, 1995, which issued as U.S.P.N. 5,879,955 on March 9, 1999, and any Information Disclosure Statement(s) submitted in the earlier application comply with 37 C.F.R.

§§ 1.98(a)-(c). In accordance with 37 C.F.R. § 1.98(d)(1) copies of the listed references are not required to be re-submitted to the Examiner.

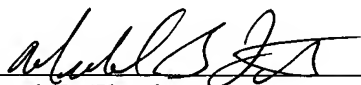
In accordance with 37 C.F.R. § 1.97, this Information Disclosure Statement is not to be construed as a representation that a search has been made, as an admission that the information cited herein is, or is considered to be, material to patentability as defined in 37 C.F.R. §1.56(b), or as a representation that no other possibly material information, as defined in 37 C.F.R. § 1.56(b), exists.

Furthermore, the references listed on the attached PTO-1449 Form are not to be construed as an admission that these references qualify as prior art as to the above-referenced application or any related application. Rather, these references are being presented for the Examiner's consideration without prejudice to Applicants' right to demonstrate that any of these references do not qualify as prior art should the Examiner choose to apply any of these references.

The following information is listed below in accordance with 37 C.F.R. §1.98. Any explanation of non-English language documents contained in this Information Disclosure Statement is believed to constitute a concise explanation of the relevance of the listed reference as it is presently understood by the individual designated in § 1.56(c) most knowledgeable about the content of the listed reference, in accordance with 37 C.F.R. § 1.98(a)(3).

Respectfully submitted,

Date: February 18, 2004

  
\_\_\_\_\_  
Michael G. Fletcher  
Reg. No. 32,777  
Fletcher Yoder  
P.O. Box 692289  
Houston, Texas 77269-2289  
(281) 970-4545

**Form PTO-1449** (modified)List of Patents and Publications  
For Applicant's Information

Disclosure Statement

(Use several sheets if necessary)

ATTY. DOCKET NO.  
MCRO:017-7/FLESERIAL NO.  
UnassignedAPPLICANT  
Fernando Gonzalez et al.FILING DATE  
HerewithGROUP  
Unassigned**U.S. PATENT DOCUMENTS**

EXAM. INIT.	REF. DES.	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE
	A1	3,241,009	03/15/66	Dewald et al.	317	234	11/06/61
	A2	3,423,646	01/21/69	Cubert et al.	317	234	02/01/65
	A3	3,602,635	08/31/71	Romankiw	174	68.5	06/30/70
	A4	3,699,543	10/17/72	Neale	340	173R	12/22/69
	A5	3,796,926	03/12/74	Colé et al.	317	234 R	03/29/71
	A6	3,877,049	04/08/75	Buckley	357	2	11/28/73
	A7	3,886,577	05/27/75	Buckley	357	2	09/12/73
	A8	4,099,260	07/04/78	Lynes et al.	365	105	09/20/76
	A9	4,115,872	09/19/78	Bluhm	365	163	05/31/77
	A10	4,174,521	11/13/79	Neale	357	45	04/06/78
	A11	4,194,283	03/25/80	Hoffmann	29	571	08/16/78
	A12	4,227,297	10/14/80	Angerstein	29	571	07/31/78
	A13	4,203,123	05/13/80	Shanks	357	2	12/12/77
	A14	4,272,562	06/09/81	Wood	427	87	06/19/79
	A15	4,420,766	12/13/83	Kasten	357	59	02/09/81
	A16	4,433,342	02/21/84	Patel et al.	357	2	04/06/81
	A17	4,458,260	07/03/84	McIntyre et al.	357	30	11/20/81
	A18	4,499,557	02/12/85	Holmberg et al.	365	163	07/06/81
	A19	4,502,208	03/05/85	McPherson	29	584	08/26/83
	A20	4,502,914	03/05/85	Trumpf et al.	156	643	10/28/83
	A21	4,569,698	02/11/86	Feist	148	1.5	05/31/85
	A22	4,630,355	12/23/86	Johnson	29	575	03/08/85
	A23	4,641,420	02/10/87	Lee	29	511	08/30/84
	A24	4,642,140	02/10/87	Noufi et al.	148	6.24	04/30/85
	A25	4,666,252	05/19/87	Yaniv et al.	350	333	06/29/84

	A26	4,677,742	07/07/87	Johnson	29	591	12/05/83
	A27	4,757,359	07/12/88	Chiao et al.	357	23.5	04/07/86
	A28	4,795,657	01/03/89	Formigoni et al.	427	96	04/08/85
	A29	4,804,490	02/14/89	Pryor et al.	252	62.3 BT	10/13/87
	A30	4,809,044	02/28/89	Pryor et al.	357	2	11/26/86
	A31	4,823,181	04/18/89	Mohsen et al.	357	51	05/09/86
	A32	4,876,220	10/24/89	Mohsen et al.	437	170	11/13/87
	A33	4,876,668	10/24/89	Thakoor et al.	365	163	04/29/86
	A34	4,881,114	11/14/89	Mohsen et al.	357	54	05/16/86
	A35	4,892,840	01/09/90	Esquivel et al.	437	52	04/11/89
	A36	5,144,404	09/01/92	Iranmanesh et al.	357	51	08/22/90
	A37	5,166,096	11/24/92	Cote et al.	437	195	04/14/92
	A38	5,166,758	11/24/92	Ovshinsky et al.	257	3	01/18/91
	A39	5,177,567	01/05/93	Klersy et al.	257	4	07/19/91
	A40	5,216,282	06/01/93	Cote et al.	257	773	10/29/91
	A41	5,233,217	08/03/93	Dixit et al.	257	530	05/03/91
	A42	5,293,335	03/08/94	Pernisz et al.	365	148	12/09/92
	A43	5,296,716	03/22/94	Ovshinsky et al.	257	3	08/19/91
	A44	5,310,693	05/10/94	Hsue	437	43	06/24/93
	A45	5,335,219	08/02/94	Ovshinsky et al.	369	288	09/30/91
	A46	5,341,328	08/23/94	Ovshinsky et al.	365	163	06/15/92
	A47	5,359,205	10/25/94	Ovshinsky	257	3	05/08/92
	A48	5,363,329	11/08/94	Troyan	365	184	11/10/93
	A49	5,406,125	04/11/95	Johnson et al.	257	774	04/15/93
	A50	5,414,271	05/09/95	Ovshinsky et al.	257	3	11/07/91
	A51	5,429,988	07/04/95	Huang et al.	437	187	06/13/94
	A52	5,510,629	04/23/96	Karpovich et al.	257	50	05/27/94
	A53	5,534,711	07/09/96	Ovshinsky et al.	257	3	04/19/95
	A54	5,534,712	07/09/96	Ovshinsky et al.	217	3	08/21/95
	A55	5,536,947	07/16/96	Klersy et al.	257	3	07/25/95
	A56	5,569,932	10/29/96	Shor et al.	257	3	01/23/95
	A57	5,578,185	11/26/96	Bergeron et al.	205	123	01/31/95
	A58	5,675,187	10/07/97	Numata et al.	257	758	05/16/96

## FOREIGN PATENT DOCUMENTS

EXAM. INIT.	REF. DES.	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	TRANSLATION YES/NO
	B1	1 319 388	06/06/73	Great Britain	H01L	9/00	Yes
	B2	0 117 045	08/29/84	EPA	H01L	45/00	Yes
	B3	JP 60109266	06/14/85	Japan	H01L	27/10	Yes

## OTHER ART (Author, Title, Journal, Volume, Pertinent Pages, & Date)

C1	Kim and Kim, "Effects of High-Current Pulses on Polycrystalline Silicon Diode with n-type Region Heavily Doped with Both Boron and Phosphorus," <i>J. Appl. Phys.</i> , 53(7):5359-5360, 1982.
C2	Neale and Aseltine, "The Application of Amorphous Materials to Computer Memories," <i>IEEE</i> , 20(2):195-205, 1973.
C3	Pein and Plummer, "Performance of the 3-D Sidewall Flash EPROM Cell," <i>IEEE</i> , 11-14, 1993.
C4	Post and Ashburn, "Investigation of Boron Diffusion in Polysilicon and its Application to the Design of p-n-p Polysilicon Emitter Bipolar Transistors with Shallow Emitter Junctions," <i>IEEE</i> , 38(11):2442-2451, 1991.
C5	Post <i>et al.</i> , "Polysilicon Emitters for Bipolar Transistors: A Review and Re-Evaluation of Theory and Experiment," <i>IEEE</i> , 39(7):1717-1731, 1992.
C6	Post and Ashburn, "The Use of an Interface Anneal to Control the Base Current and Emitter Resistance of p-n-p Polysilicon Emitter Bipolar Transistors," <i>IEEE</i> , 13(8):408-410, 1992.
C7	Rose <i>et al.</i> , "Amorphous Silicon Analogue Memory Devices," <i>J. Non-Crystalline Solids</i> , 115:168-170, 1989.
C8	Schaber <i>et al.</i> , "Laser Annealing Study of the Grain Size Effect in Polycrystalline Silicon Schottky Diodes," <i>J. Appl. Phys.</i> , 53(12):8827-8834, 1982.
C9	Yamamoto <i>et al.</i> , "The I-V Characteristics of Polycrystalline Silicon Diodes and the Energy Distribution of Traps in Grain Boundaries," <i>Electronics and Communications in Japan</i> , Part 2, 75(7):51-58, 1992.
C10	Yeh <i>et al.</i> , "Investigation of Thermal Coefficient for Polycrystalline Silicon Thermal Sensor Diode," <i>Jpn. J. Appl. Phys.</i> , 31(Part 1, No. 2A):151-155, 1992.
C11	Oakley <i>et al.</i> , "Pillars - The Way to Two Micron Pitch Multilevel Metallisation," <i>IEEE</i> , 23-29, 1984.
C12	Prince, "Semiconductor Memories," A Handbook of Design, Manufacture, and Application, 2 <sup>nd</sup> Ed., pgs. 118-123.

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

*Information Disclosure Statement--PTO-1449 (Modified)*